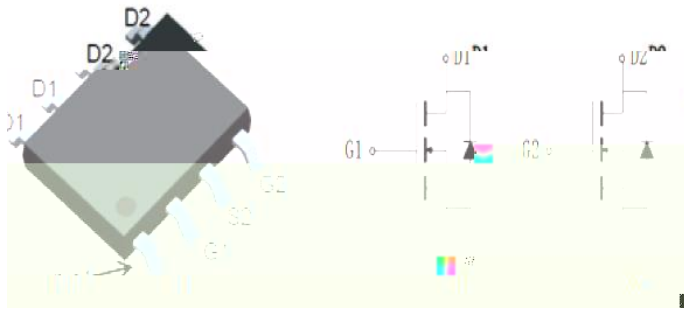




N-Channel Enhancement Mode Field Effect Transistor



Product Summary

V_{DS}	30V
I_D	8.5A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	21mohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	35mohm
100% V_{DS} Tested	

General Description

Trench Power LV MOSFET technology

YJS3404A

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Typical Performance Characteristics

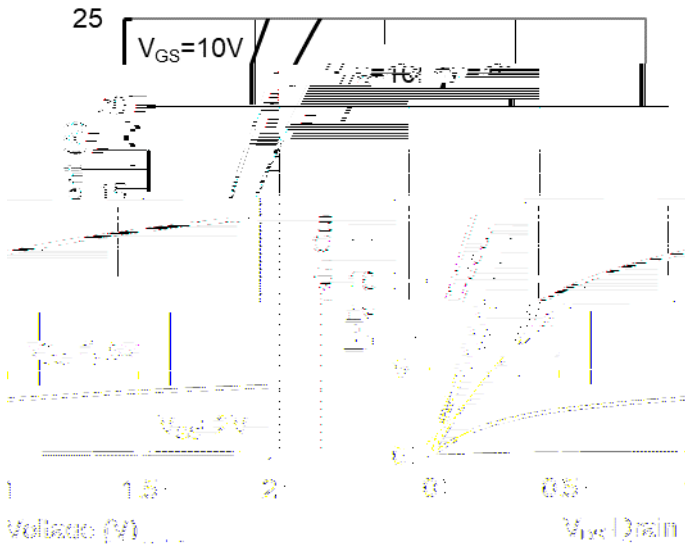


Figure1. Output Characteristics

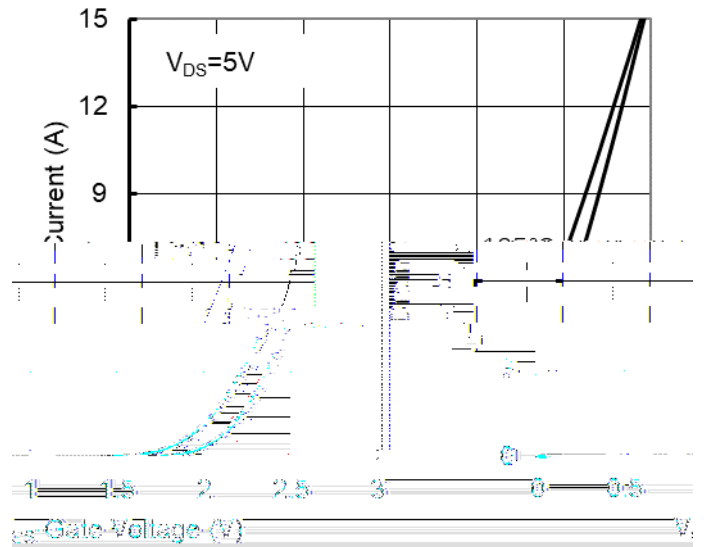


Figure2. Transfer Characteristics

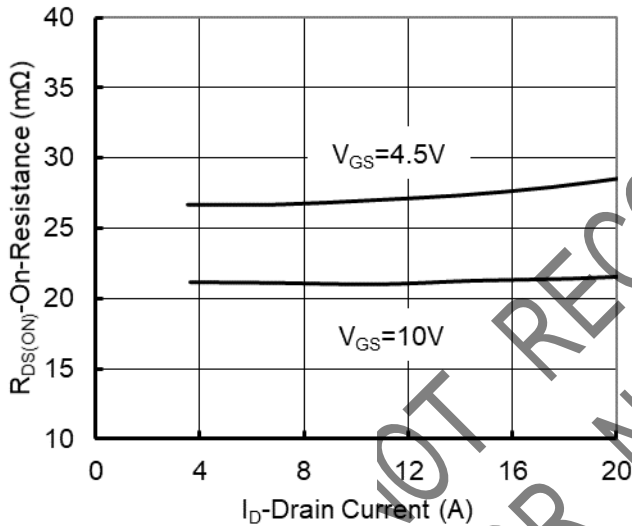


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

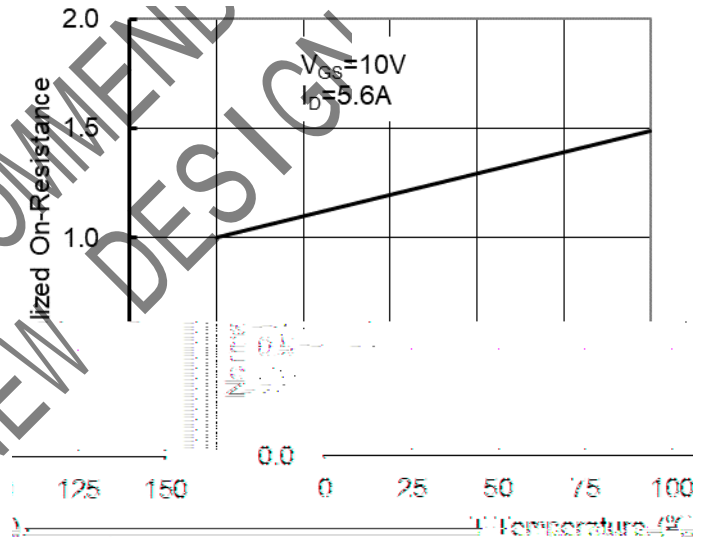


Figure 4: On-Resistance vs. Junction Temperature

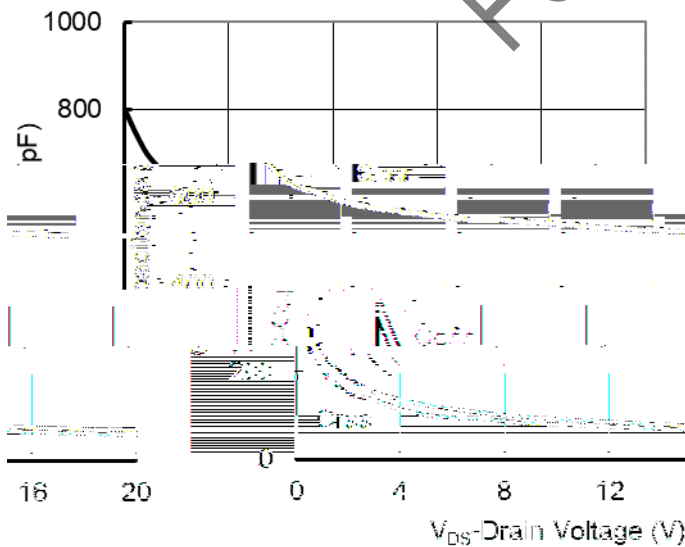


Figure5. Capacitance Characteristics

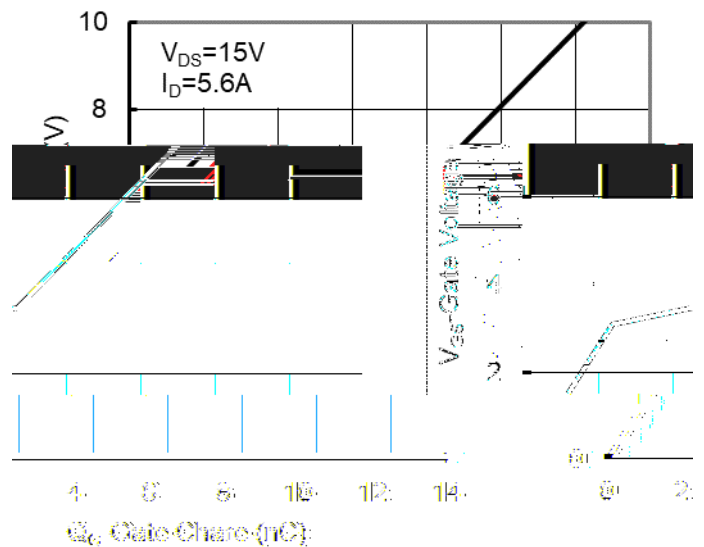
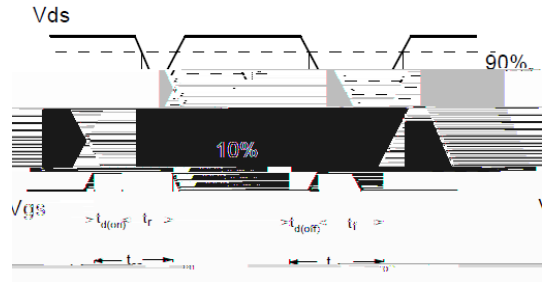
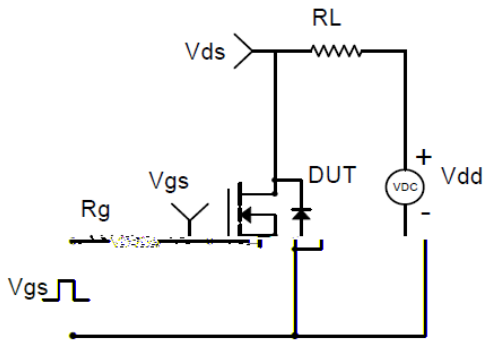


Figure6. Gate Charge

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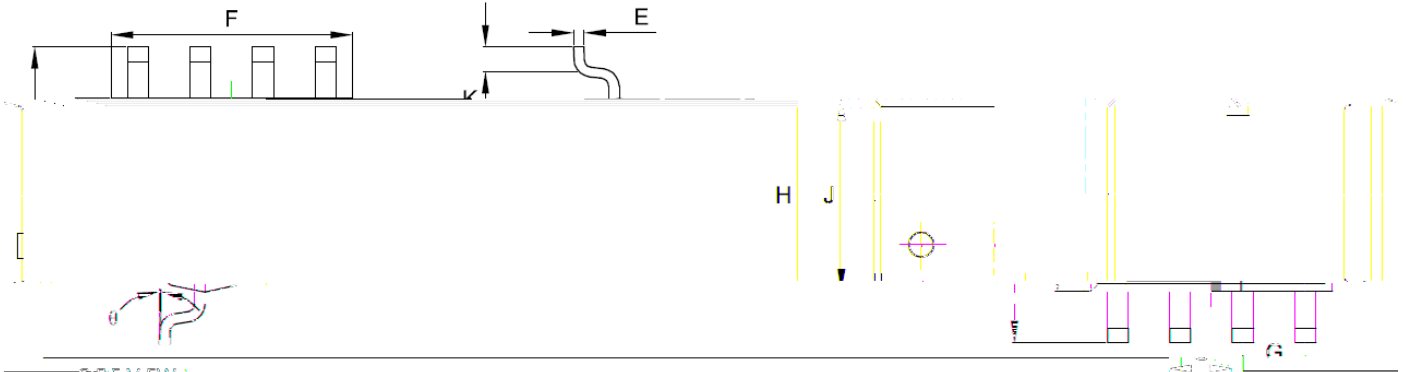
Resistive Switching



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SOP-8 Package information



SYMBOL	MIN	MAX	MIN	MAX
A	0.053	0.069	1.950	1.750
B	0.004	0.010	0.100	0.250
C	0.053	0.061	1.350	1.550
D	0.013	0.020	0.930	0.510
E	0.017	0.020	0.250	0.250
G	0.050BSC	0.050BSC	1.270BSC	1.270BSC
J	0.150	0.157	3.800	4.000
K	0.016	0.050	0.400	1.270

NOT RECOMMEND
FOR NEW DESIGN



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